

B.M.S. College of Engineering, Bengaluru-560019

Autonomous Institute Affiliated to VTU

April 2024 Semester End Main Examinations

Programme: B.E.

Branch: Electronics and Communication Engineering

Course Code: 22EC3PCAEC

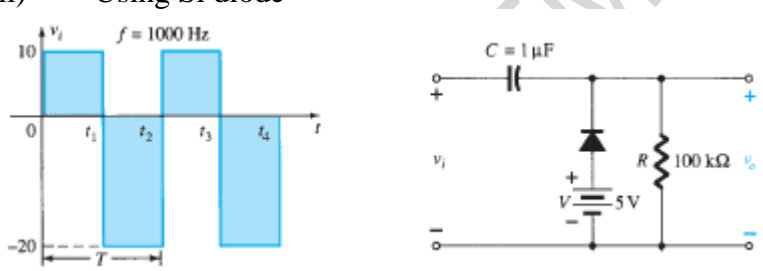
Course: Analog Electronic Circuits

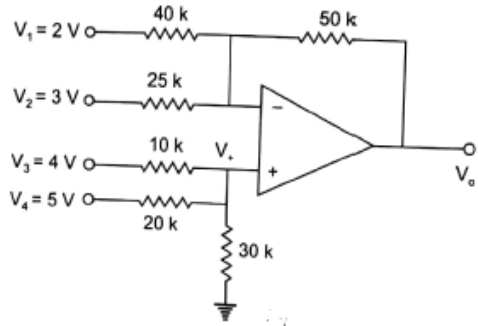
Semester: III

Duration: 3 hrs.

Max Marks: 100

Instructions: 1. Answer any FIVE full questions, choosing one full question from each unit.
2. Missing data, if any, may be suitably assumed.

Important Note: Completing your answers, compulsorily draw diagonal cross lines on the remaining blank pages. Revealing of identification, appeal to evaluator will be treated as malpractice.			UNIT - I	CO	PO	Marks
	1	a)	Analyze the given circuit in Fig 1, determine the output voltage and plot the output waveform for the circuit given below: i) Using ideal diode ii) Using Si diode  Fig-1	CO3	PO 2	10
		b)	Deduce the small signal r_e equivalent model for the voltage divider configuration circuit. Also obtain the expressions for A_v , z_i and z_o .	CO 2	PO 1	10
			UNIT - II			
	2	a)	Derive expressions for gain, input resistance and output resistance of voltage shunt feedback with block representation approach.	CO 2	PO 1	10
		b)	What is the drawback of the Class B Power Amplifier? Explain the measures to overcome the same with suitable diagrams	CO 1	-	5
		c)	Suggest a suitable method to increase the efficiency of series fed Class A Power Amplifier and deduce an expression to prove the efficiency is higher than Series fed Class A type.	CO 2	PO 1	5
			UNIT - III			
	3	a)	An enhancement type NMOS transistor with $V_t=0.7V$ conducts a current $I_D=100\mu A$ when $V_{GS}=V_{DS}=1.2V$. Find the value of I_D for $V_{GS}=1.5V$ and $V_{DS}=3V$. Also calculate the value of the drain to source resistance R_{DS} for small V_{DS} and $V_{GS}=3.2V$.	CO 2	PO 1	10
		b)	Derive an expression for drain current of NMOS transistor that operates in i) Triode region ii) Saturation region	CO 2	PO 1	10

		OR			
4	a)	Determine and comment on the drain currents for a n-channel MOSFET with $t_{ox} = 20 \text{ nm}$, $\mu_n = 650 \text{ cm}^2/\text{V.s}$, $V_t = 0.8 \text{ V}$, and $W/L = 10$. (a) $V_{GS} = 5 \text{ V}$ and $V_{DS} = 1 \text{ V}$. (b) $V_{GS} = 2 \text{ V}$ and $V_{DS} = 1.2 \text{ V}$. (c) $V_{GS} = 5 \text{ V}$ and $V_{DS} = 0.2 \text{ V}$. (d) $V_{GS} = V_{DS} = 5 \text{ V}$	CO 2	PO 1	10
	b)	With the help of a graphical construction, obtain the transfer characteristics and deduce the condition for operation in the saturation region of a CS amplifier.	CO 2	PO 1	10
		UNIT - IV			
5	a)	Develop a T equivalent model of a MOSFET with necessary equations and diagrams	CO 2	PO 1	10
	b)	Analyze the three different relationships for determining transconductance g_m .	CO 3	PO 2	10
		UNIT - V			
6	a)	Deduce an expression for gain of a non-inverting amplifier. Denote the condition and describe the condition for a voltage follower	CO 2	PO 1	10
	b)	For a certain application it is required to convert a voltage signal to proportional output current. Identify the circuit which performs the function and describe the different types.	CO 2	PO 1	10
		OR			
7	a)	Determine V_o for the adder subtractor circuit shown in Fig-2  Fig-2	CO 2	PO 1	10
	b)	Derive an expression for time period "T" for monostable multivibrator using 555. Describe the working with necessary timing diagram.	CO 2	PO 1	10
